

Search 10/710,453

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	6061	(gate near thickness) and (threshold near voltage)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 07:46
L8	2984	L7 and CMOS	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 07:46
L9	1345	L8 and leakage	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 07:46
L10	585	L9 and ((power near consumption) or (power near dissipation))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 07:46
L11	329	L10 and thin and thick	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 07:46
L12	54	L11 and (low near threshold) and (high near threshold)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 07:46
L13	3	12 and monotonic\$5	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 08:17
L14	852	(326/81).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/15 08:16
L15	6	14 and monotonic\$5	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 08:18
L16	33	7 and 14	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 08:18
S1	28	low near leakage near CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:30
S2	2	reduced near leakage near CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:20
S3	0	reduced near leakage near (complementary adj metal adj oxide adj semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:19
S4	0	low near leakage near (complementary adj metal adj oxide adj semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:19

10/710, 453

S5	51	multi-threshold near voltages	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:38
S6	73	multi near threshold near voltages	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:39
S7	73	S5 or S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:39
S8	0	S7 and (thin near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:40
S9	1	S7 and (thick near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:40
S10	39	S7 and leakage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:41
S11	3	("5917333" "5942910" "6310487").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 14:48
S12	17	("4894558" "5107230" "5216289" "5491429" "5537060" "5614847" "5617043" "5751651" "5773999" "5781062" "5801576" "5852579" "5877647" "5889415" "5929687" "6031778" "6034563").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 14:53
S13	4293	((326/93,95,98) or (327/208-212,214,215,224,225)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 14:54
S14	81	S13 and (low near threshold) and (high near threshold)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:42
S15	6	S14 and (thin near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:56

10/710,453

S16	1	S14 and (thin near gate) and (thick near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:56
S17	138	(326/29).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 15:49
S18	125303	((("327") or ("326")).CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 15:50
S19	5995	S18 and (cascade or cascading)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:50
S20	905	S18 and (pipeline or pipeling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:50
S21	20	S18 and (pipe-line or pipe-ling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:51
S22	917	S20 or S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:51
S23	6775	S19 or S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:51
S24	68	S23 and (gate near thickness)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:03
S25	1	("20020008999").PN.	US-PGPUB	OR	OFF	2005/12/05 16:04
S26	15	("20020000872" "20020079542" "3806741" "4672243" "5512771" "5610533" "5880604" "5909140" "5942784" "5985706" "6133762" "6255698" "6307234" "6333541" "6529042").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 07:29
S27	6027	(gate near thickness) and (threshold near voltage)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 07:30
S28	2970	S27 and CMOS	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 07:30

10/710,453

S29	1335	S28 and leakage	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 07:31
S30	581	S29 and ((power near consumption) or (power near dissipation))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 07:32
S31	327	S30 and thin and thick	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 07:32
S32	322	S31 and low and high	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 07:33
S33	54	S31 and (low near threshold) and (high near threshold)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/15 07:46